BYC10DX-600



Hyperfast power diode Rev. 1 — 30 June 2011

Product data sheet

Product profile 1.

1.1 General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- Isolated plastic package
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

1.3 Applications

Continuous Current Mode (CCM) Power Factor Correction (PFC)

- Half-bridge/full-bridge switched-mode power supplies
- Half-bridge lighting ballasts

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; $T_h = 41$ °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	10	Α
Static char	racteristics					
V _F	forward voltage	I _F = 10 A; T _j = 25 °C; see <u>Figure 5</u>	-	2	2.5	V
		$I_F = 10 \text{ A}; T_j = 150 \text{ °C};$ see Figure 5	-	1.4	1.8	V
Dynamic o	haracteristics					
t _{rr}	reverse recovery time	$I_F = 10 \text{ A}; V_R = 400 \text{ V};$ $dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 ^{\circ}\text{C}; \text{ see } \frac{\text{Figure 6}}{\text{C}}$	-	18	-	ns



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		v. 14 .
2	Α	anode	mb	K — A 001aaa020
mb	n.c.	mounting base; isolated	SOD113 (TO-220F)	

3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
BYC10DX-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113	

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	500	V
$I_{F(AV)}$	average forward current	square-wave pulse; δ = 0.5 ; T _h = 41 °C; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	10	Α
I _{FRM}	repetitive peak forward current	square-wave pulse; $\delta = 0.5$; $t_p = 25~\mu s;$ $T_h = 41~^{\circ} C$	-	20	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; see Figure 3	-	65	Α
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C; see Figure 3	-	71	Α
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	150	°C

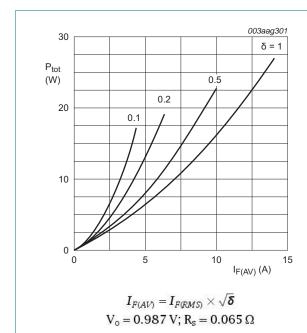
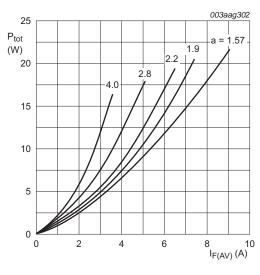
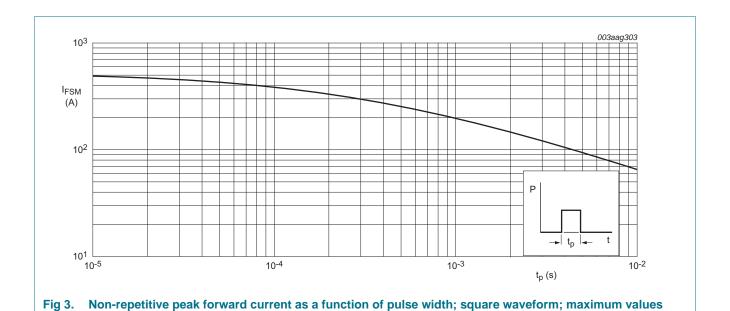


Fig 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



a = form factor = $I_{F(RMS)}/I_{F(AV)}$ $V_0 = 0.987 \text{ V}; R_s = 0.065 \Omega$

Fig 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
()/	thermal resistance from junction to	without heatsink compound	-	-	5.9	K/W
	heatsink	with heatsink compound; see Figure 4	-	-	4.8	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air		-	60	-	K/W

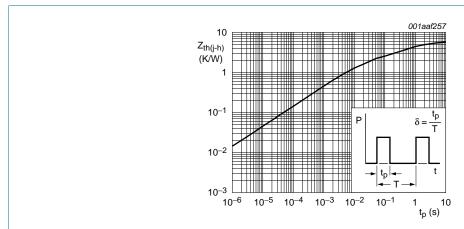


Fig 4. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

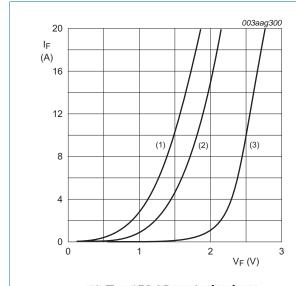
Table 6. Isolation characteristics

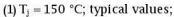
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz ; from cathode to external heatsink	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _F	forward voltage	$I_F = 10 \text{ A}; T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{\text{Minimum 5}}$	-	2	2.5	V
		$I_F = 10 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.4	1.8	V
		$I_F = 20 \text{ A}; T_j = 150 \text{ °C}; \text{ see } \frac{\text{Figure 5}}{}$	-	1.7	2.2	V
I _R rev	reverse current	$V_R = 500 \text{ V}; T_j = 100 ^{\circ}\text{C}$	-	1.1	3	mΑ
		V _R = 600 V	-	9	200	μΑ
Dynamic ch	naracteristics					
t _{rr}	reverse recovery time	$I_F = 1 \text{ A; } V_R = 30 \text{ V; } dI_F/dt = 50 \text{ A/}\mu\text{s;}$ $T_j = 25 \text{ °C; see } \frac{\text{Figure 6}}{\text{ Composition}}$	-	15	30	ns
		$I_F = 10 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 6	-	18	-	ns
I _{RM}	peak reverse recovery current	$I_F = 10 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 500 \text{ A/}\mu\text{s}$; $T_j = 100 \text{ °C}$; see Figure 6	-	9.5	12	Α
		$I_F = 10 \text{ A}$; $V_R = 400 \text{ V}$; $dI_F/dt = 50 \text{ A/}\mu\text{s}$; $T_j = 125 \text{ °C}$; see Figure 6	-	3	7.5	Α
V_{FR}	forward recovery voltage	$I_F = 10 \text{ A}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; see Figure 7	-	8	11	V





⁽²⁾ $T_j = 150$ °C; maxium values;

(3)
$$T_j = 25$$
 °C; maxium values;

$$V_{\text{o}}$$
 = 0.987 V; R_{s} = 0.065 Ω

Fig 5. Forward current as a function of forward voltage

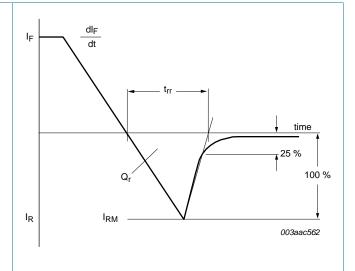
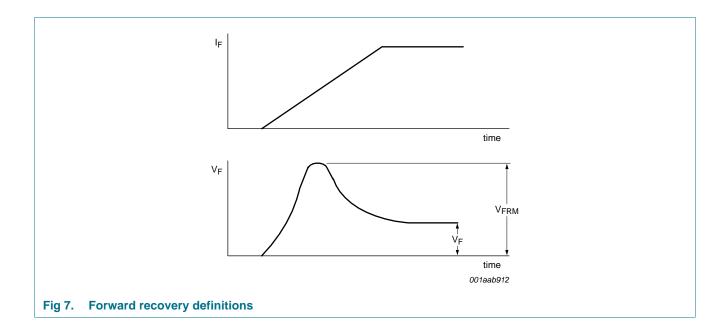


Fig 6. Reverse recovery definitions; ramp recovery



7 of 12

8. Package outline

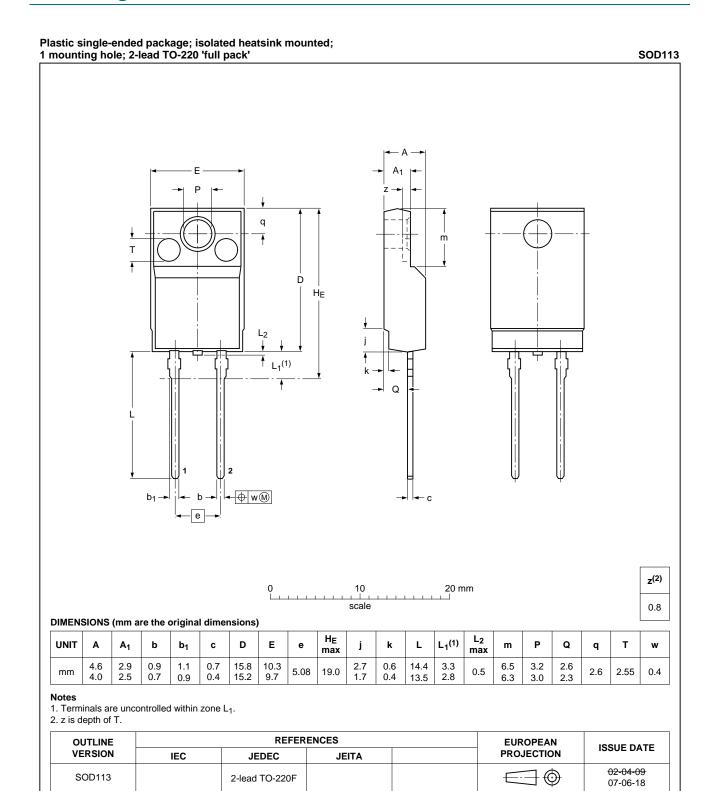


Fig 8. Package outline SOD113 (TO-220F)

BYC10DX-600

Hyperfast power diode

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYC10DX-600 v.1	20110630	Product data sheet	-	-

10. Legal information

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Product [short] data sheet	Production	This document contains the product specification.

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11 of 12

BYC10DX-600

Hyperfast power diode

12. Contents

1	Product profile
1.1	General description
1.2	Features and benefits1
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information
4	Limiting values
5	Thermal characteristics5
6	Isolation characteristics
7	Characteristics6
8	Package outline
9	Revision history9
10	Legal information10
10.1	Data sheet status
10.2	Definitions10
10.3	Disclaimers
10.4	Trademarks11
11	Contact information11

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